1. General description

The 74LVC2G00 provides a 2-input NAND gate function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information									
Type number	Package	Package							
	Temperature range	Name	Description	Version					
74LVC2G00DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2					
74LVC2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
74LVC2G00GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1					
74LVC2G00GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089					
74LVC2G00GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2					
74LVC2G00GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2					
74LVC2G00GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116					
74LVC2G00GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203					

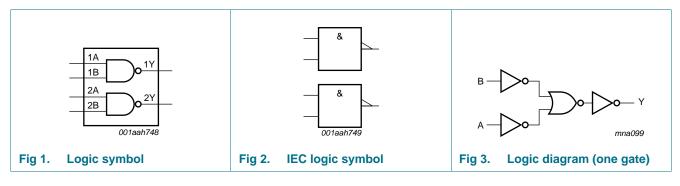
4. Marking

Table 2.Marking codes

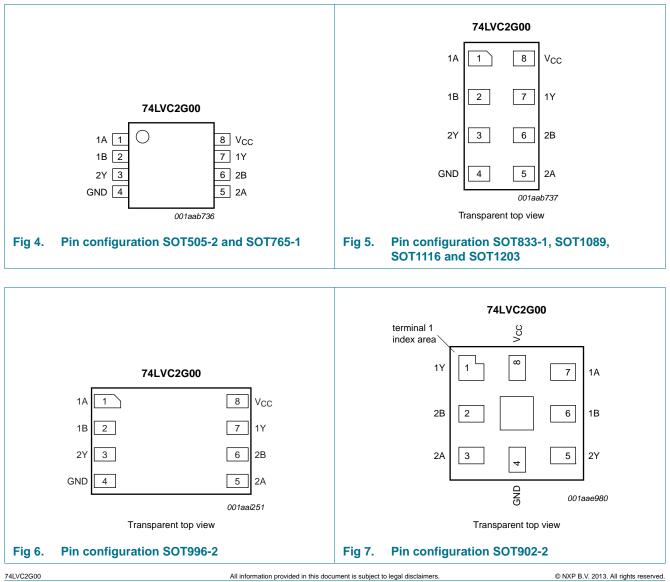
Type number	Marking code ^[1]
74LVC2G00DP	V2G00
74LVC2G00DC	V00
74LVC2G00GT	V00
74LVC2G00GF	VA
74LVC2G00GD	V00
74LVC2G00GM	V00
74LVC2G00GN	VA
74LVC2G00GS	VA

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information



6.1 Pinning

6.2 Pin description

Symbol	Pin	Pin			
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2			
1A, 2A	1, 5	7, 3	data input		
1B, 2B	2, 6	6, 2	data input		
GND	4	4	ground (0 V)		
1Y, 2Y	7, 3	1, 5	data output		
V _{cc}	8	8	supply voltage		

7. Functional description

Table 4. Function table^[1]

Input		Output
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	<u>[1]</u> –0.5	V _{CC} + 0.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
I _{OK}	output clamping current	V_{O} < 0 V or V_{O} > V_{CC}	-	±50	mA
I _O	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[3]	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0 V$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of Ptot derates linearly with 8 mW/K.

For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	10	ns/V
		100 = 11 10 010 1			

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	, 0	, 0	0	,			
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C <u>[1]</u>						
V _{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V		$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V		1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V		2.0	-	-	V
	V_{CC} = 4.5 V to 5.5 V		$0.7\times V_{CC}$	-	-	V	
V _{IL}	V _{IL} LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V		-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V		-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V		-	-	$0.3 \times V_{CC}$	V
V _{OH} HIGH-I	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O} = -100 \ \mu A$; $V_{CC} = 1.65 \ V$ to 5.	5 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.2	1.53	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.9	2.13	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$		2.2	2.50	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.3	2.60	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$		3.8	4.10	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 1.65 \ V \ to \ 5.5$	V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$		-	0.08	0.45	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	0.14	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$		-	0.19	0.4	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	0.37	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$		-	0.43	0.55	V
I _I	input leakage current	$V_{I} = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	5 V	-	±0.1	±5	μA
I _{OFF}	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 5.5 V; $V_{\rm CC}$ = 0 V		-	±0.1	±10	μΑ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 \text{ A}$	-	0.1	10	μA
Δl _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	5	500	μA
Cı	input capacitance		-	2.5	-	pF
T _{amb} = -	40 °C to +125 °C					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
VIL	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –100 $\mu\text{A};$ V_{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_0 = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_0 = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 $\mu A;$ V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
I	input leakage current	V_{I} = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 5.5 V; V_{CC} = 0 V	-	-	±20	μΑ
СС	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 \text{ A}$	-	-	40	μA
∆l _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	μA

Table 7. Static characteristics ...continued

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 8	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.2	3.5	8.6	1.2	10.8	ns
		V_{CC} = 2.3 V to 2.7 V		0.7	2.3	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 V$		0.7	3.0	5.6	0.7	7.0	ns
		V_{CC} = 3.0 V to 3.6 V		0.7	2.2	4.3	0.7	5.4	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.8	3.3	0.5	4.2	ns
C_{PD}	power dissipation capacitance	per gate; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	14	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 $f_i = input frequency in MHz;$

 $f_o = output frequency in MHz;$

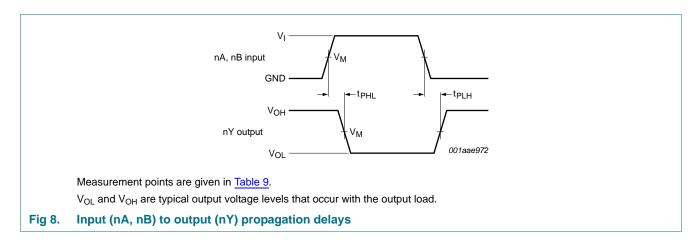
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



NXP Semiconductors

74LVC2G00

Dual 2-input NAND gate

Table 9. Measurement points				
Supply voltage	Input	Output		
V _{CC}	V _M	V _M		
1.65 V to 1.95 V	$0.5\times V_{CC}$	$0.5 imes V_{CC}$		
2.3 V to 2.7 V	$0.5\times V_{CC}$	$0.5 imes V_{CC}$		
2.7 V	1.5 V	1.5 V		
3.0 V to 3.6 V	1.5 V	1.5 V		
4.5 V to 5.5 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$		

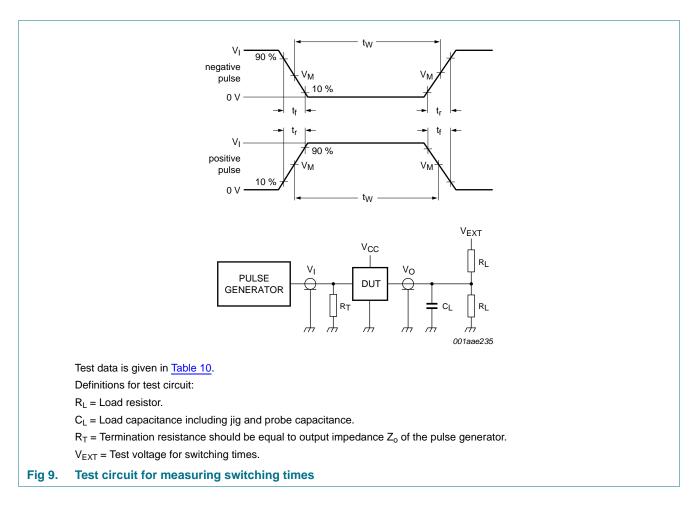


Table 10. Test data

Supply voltage	Input		Load	Load		
V _{CC}	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}	
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open	
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open	
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open	

74LVC2G00

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74LVC2G00

Dual 2-input NAND gate

13. Package outline

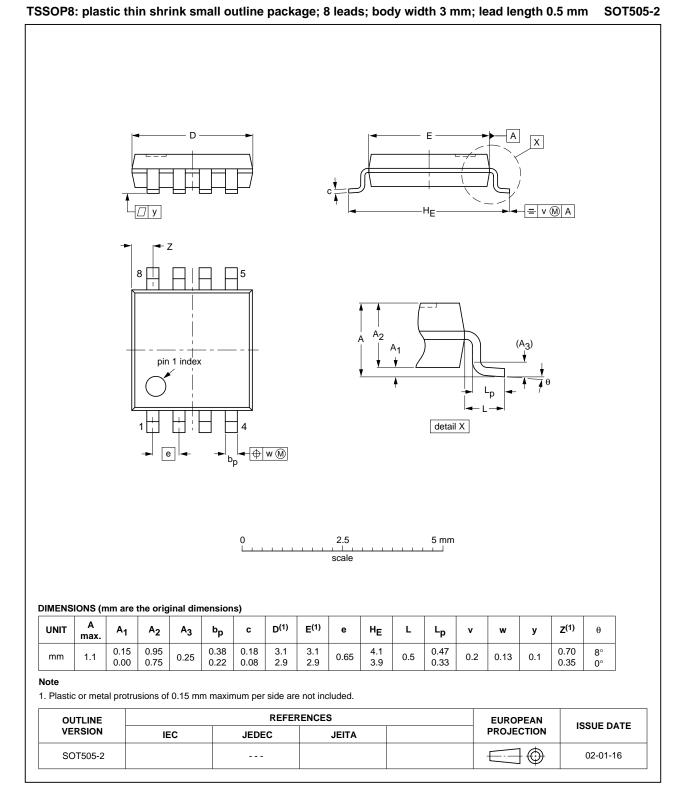


Fig 10. Package outline SOT505-2 (TSSOP8)

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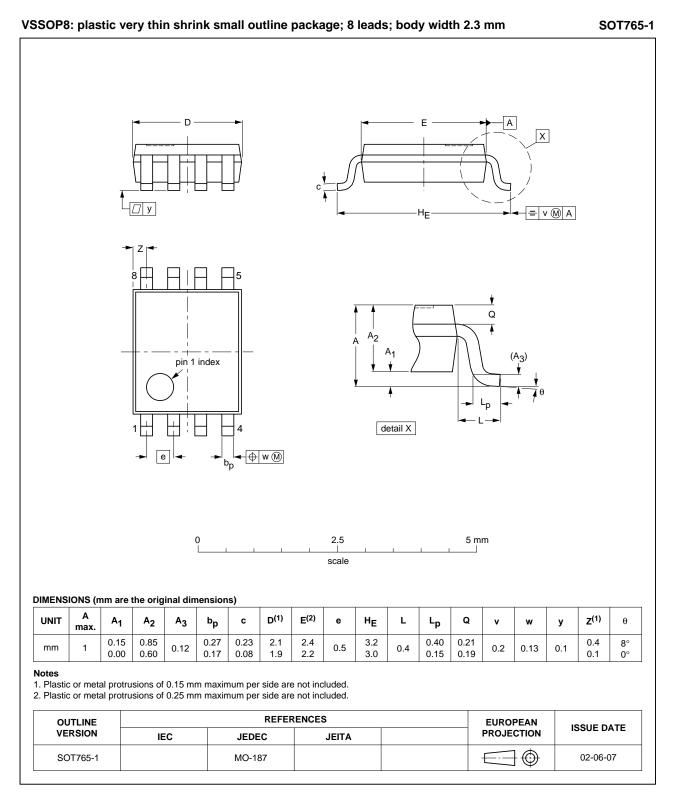


Fig 11. Package outline SOT765-1 (VSSOP8)

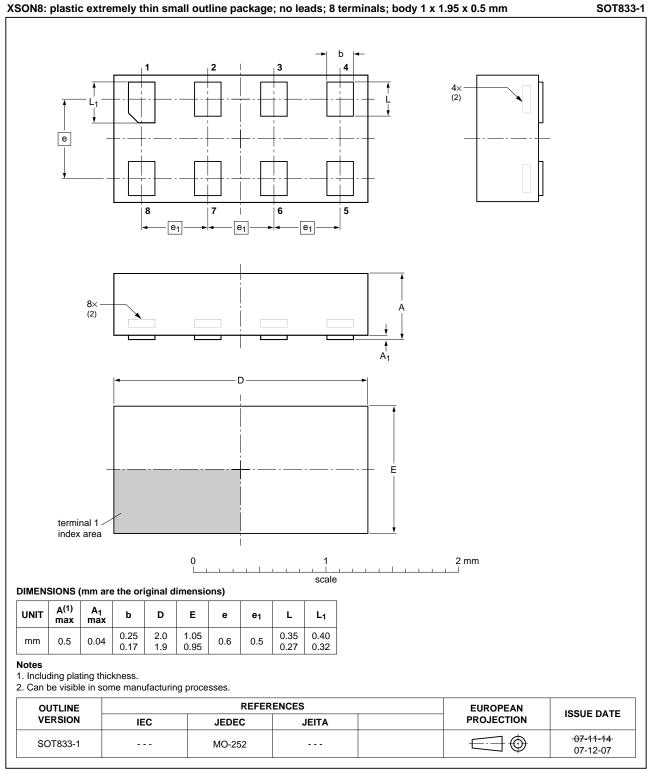
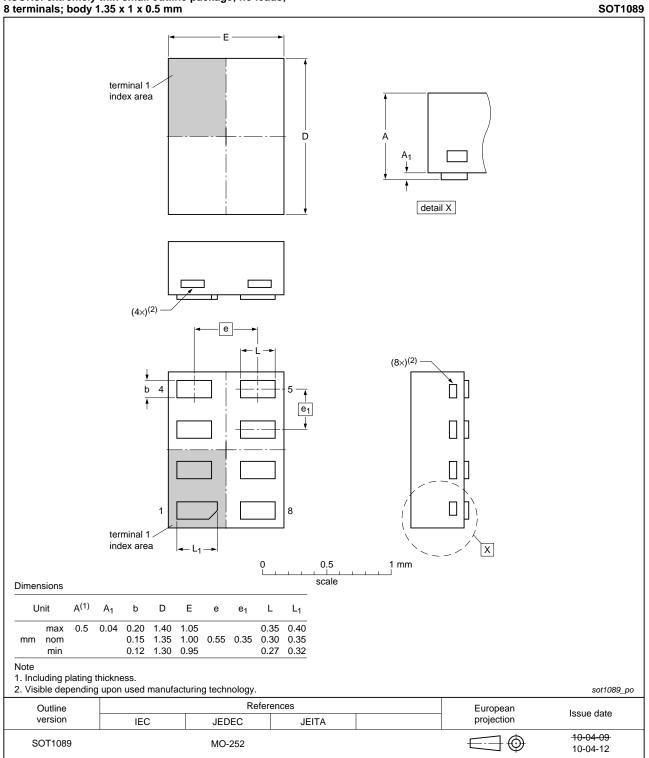


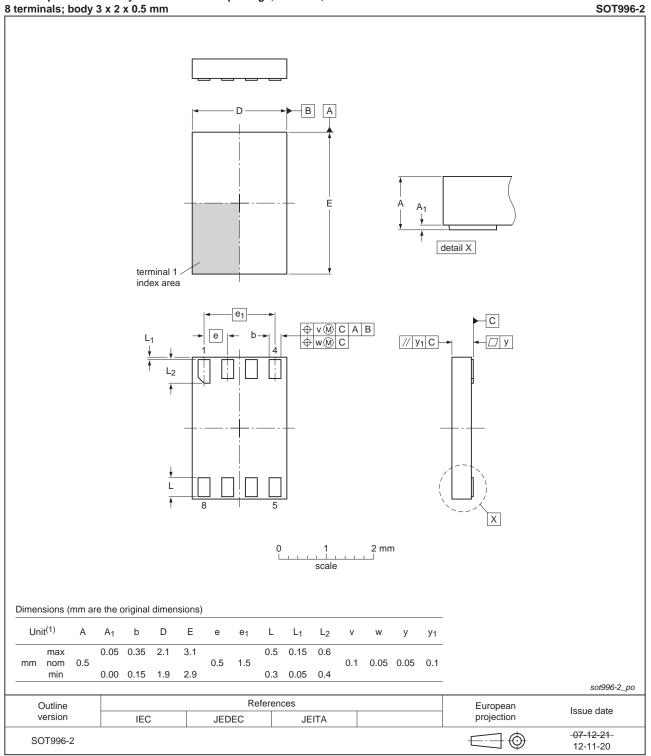
Fig 12. Package outline SOT833-1 (XSON8)



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 13. Package outline SOT1089 (XSON8)

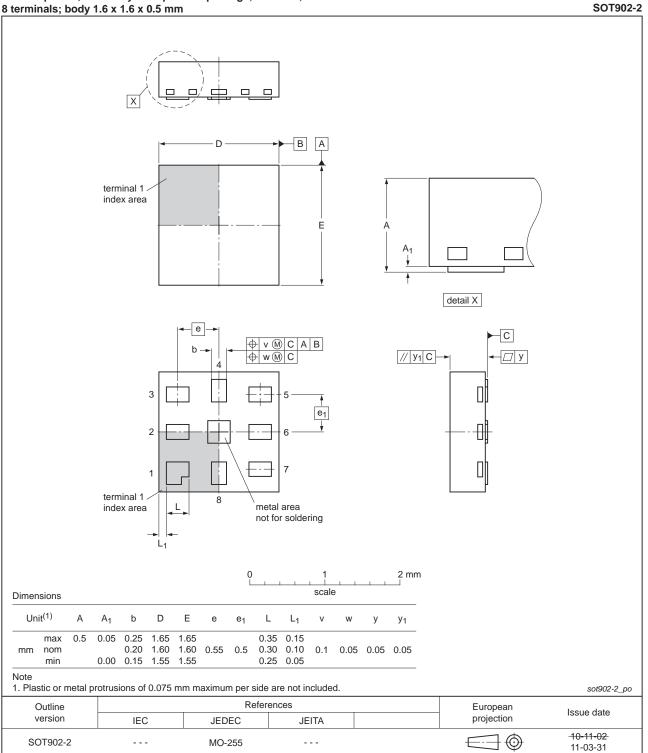
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XSON8: plastic extremely thin small outline package; no leads; 8 terminals: body 3 x 2 x 0.5 mm

Fig 14. Package outline SOT996-2 (XSON8)

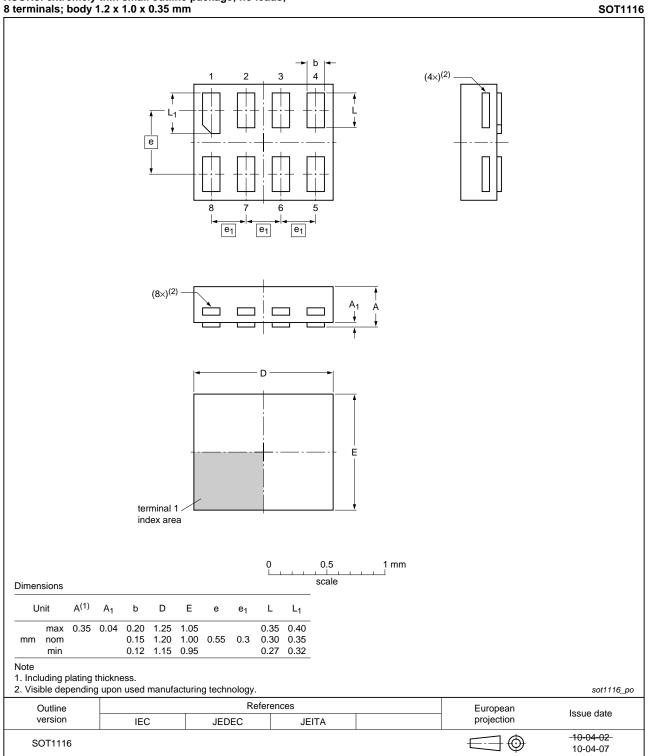
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XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 15. Package outline SOT902-2 (XQFN8)

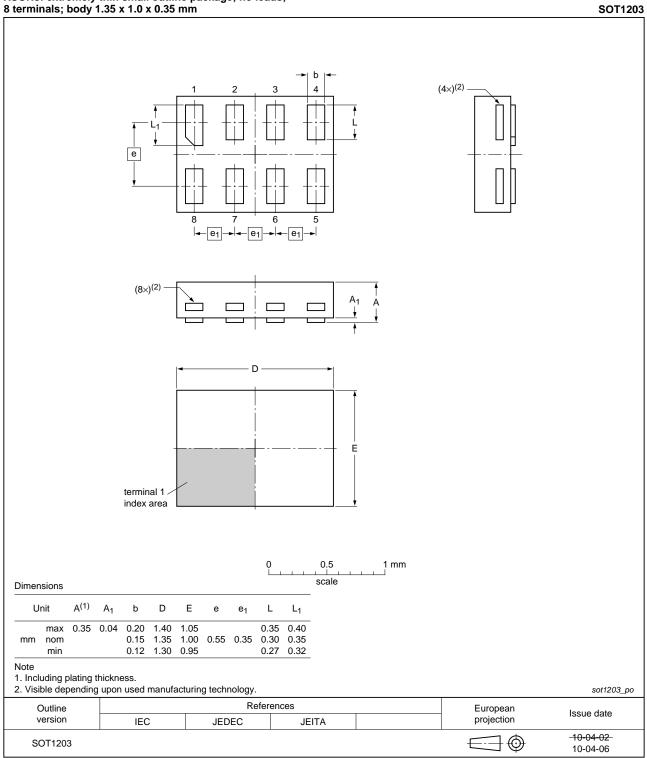
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1203 (XSON8)

14. Abbreviations

AcronymDescriptionCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Table 11. Abbreviations				
DUT Device Under Test ESD ElectroStatic Discharge HBM Human Body Model MM Machine Model	Acronym	Description			
ESD ElectroStatic Discharge HBM Human Body Model MM Machine Model	CMOS	Complementary Metal-Oxide Semiconductor			
HBM Human Body Model MM Machine Model	DUT	Device Under Test			
MM Machine Model	ESD	ElectroStatic Discharge			
	HBM	Human Body Model			
TTL Transistor-Transistor Logic	MM	Machine Model			
	TTL	Transistor-Transistor Logic			

15. Revision history

Table 12. **Revision history Document ID Release date** Data sheet status **Change notice Supersedes** 74LVC2G00 v.12 20130408 Product data sheet 74LVC2G00 v.11 -Modifications: For type number 74LVC2G00GD XSON8U has changed to XSON8. 74LVC2G00 v.11 Product data sheet 74LVC2G00 v.10 20120622 Modifications: For type number 74LVC2G00GM the SOT code has changed to SOT902-2. 74LVC2G00 v.10 Product data sheet 74LVC2G00 v.9 20111130 _ Modifications: • Legal pages updated. 74LVC2G00 v.9 20100608 Product data sheet 74LVC2G00 v.8 _ 74LVC2G00 v.8 20091026 Product data sheet 74LVC2G00 v.7 _ 74LVC2G00 v.7 20080610 Product data sheet 74LVC2G00 v.6 _ 74LVC2G00 v.6 20080220 Product data sheet 74LVC2G00 v.5 -74LVC2G00 v.5 20070904 Product data sheet 74LVC2G00 v.4 -74LVC2G00 v.4 20060515 Product data sheet 74LVC2G00 v.3 -74LVC2G00 v.3 20050201 Product specification 74LVC2G00 v.2 -74LVC2G00 v.2 20040923 Product specification 74LVC2G00 v.1 -74LVC2G00 v.1 20031117 Product specification _ _

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Dual 2-input NAND gate

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